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Data Sheet

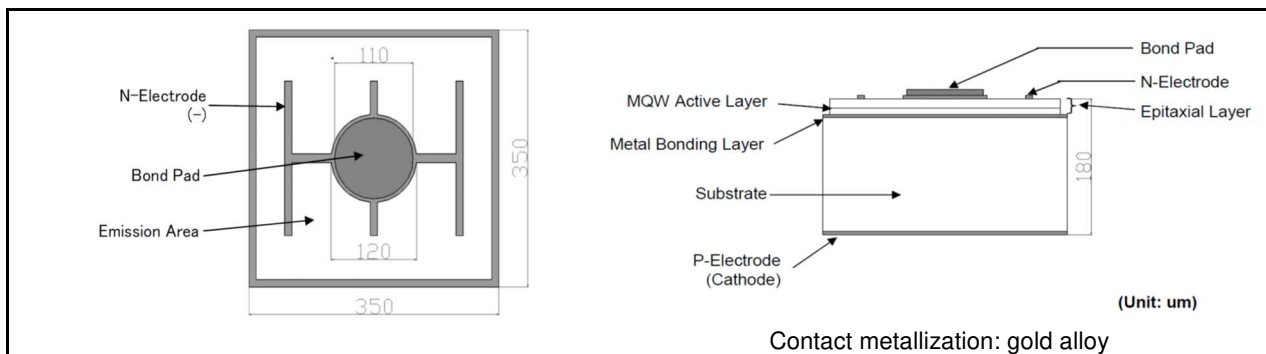
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Infrared LED Chip

EOLC-950-27D

Rev. 03, 2020

Radiation	Type	Electrodes
Infrared	InAlGaAs epitaxial layer, MQW / Si	n (cathode) up



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.25		V
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e		7		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		950		nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		27		nm
Rise time	$I_F = 20 \text{ mA}$	t_r		11		ns
Fall time	$I_F = 20 \text{ mA}$	t_f		10		ns

*Measured on bare chip on TO-18 header

Packing

Dice on adhesive film with wire bond side up.

Art. No. 131 164



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.